

FIG. 1

Figure 2. Thicknes: DC results for the medium deposition process.

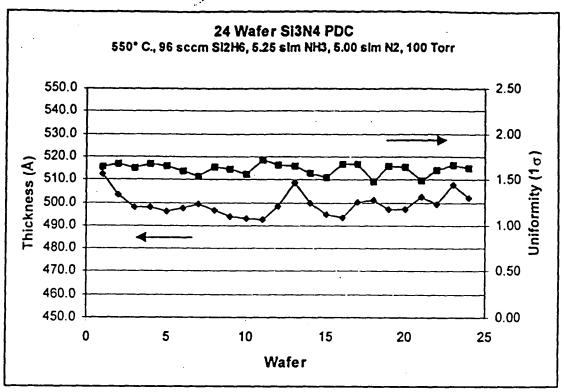


Figure 3. RI PDC results for the medium deposition rate process.

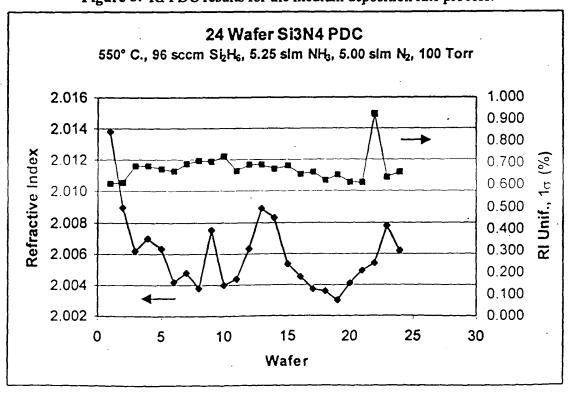
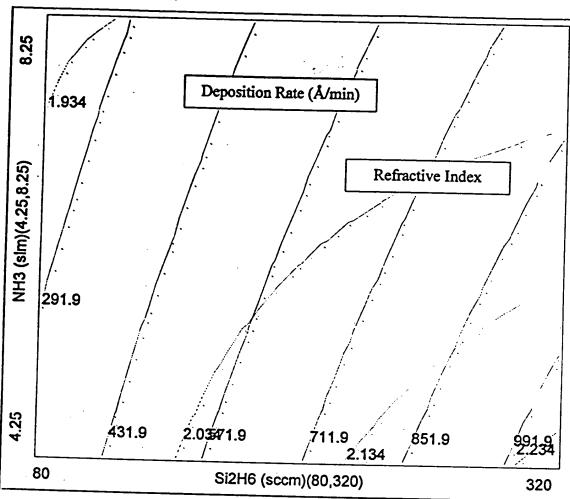
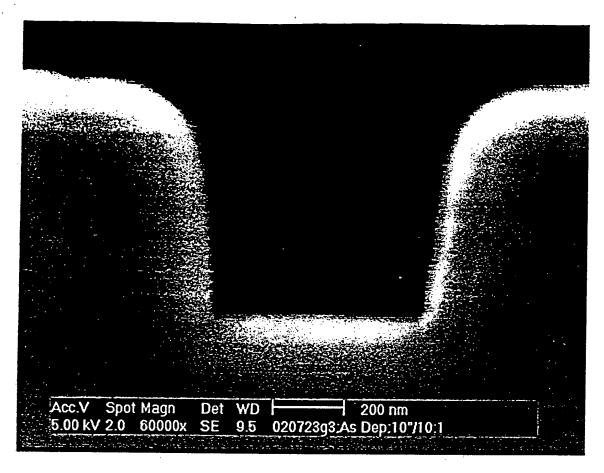


Figure 4. Effects of Si₂H₆ and NH₃ on the deposition rate and RI at constant pressure, temperature and N2 flow.





550°C Si₂H₆-based silicon nitride (deposition rate: 500 Å/min)

FIGURE 5